(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
9 January 2003 (09.01.2003)

PCT

(10) International Publication Number
WO 03/003118 A2

(51) International Patent Classification[7]: G03F 1/00

(21) International Application Number: PCT/US02/20016

(22) International Filing Date: 21 June 2002 (21.06.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/895,511 29 June 2001 (29.06.2001) US

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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

**Published:**
— *without international search report and to be republished upon receipt of that report*

*For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.*

WO 03/003118 A2

(54) Title: MASK REPAIR WITH ELECTRON BEAM-INDUCED CHEMICAL ETCHING

(57) Abstract: The present invention discloses a method of fabricating and repairing a mask without damage and an apparatus including a holder to mount a substrate; a stage to position the holder in a chamber; a pumping system to evacuate the chamber; an imaging system to locate an opaque defect in the substrate; a gas delivery system to dispense a reactant gas towards the defect; and an electron delivery system to direct electrons towards the opaque defect.